

```
graph TD; 110[PROVIDE COATED SILICON SUBSTRATE] --> 120[DEPOSIT ELECTRODE]; 120 --> 135[BACK-ETCH SUBSTRATE TO FORM MEMBRANE]; 135 --> 145[SPIN ON DIELECTRIC FILM]; 145 --> 155[FORM ELECTRET];
```

110 PROVIDE COATED SILICON SUBSTRATE

120 DEPOSIT ELECTRODE

135 BACK-ETCH SUBSTRATE TO FORM MEMBRANE

145 SPIN ON DIELECTRIC FILM

155 FORM ELECTRET

LPCVD nitride

105

100

Cr/Au electrode

115

110

KOH etch

100

130

Handwritten notes: 420, 433.03

A cross-sectional view of a substrate 130. A Teflon AF film 140 is applied to the top surface of the substrate 130. The substrate 130 has a central rectangular region and four trapezoidal regions on the sides, all containing a conductive layer 120.

FIG. 1

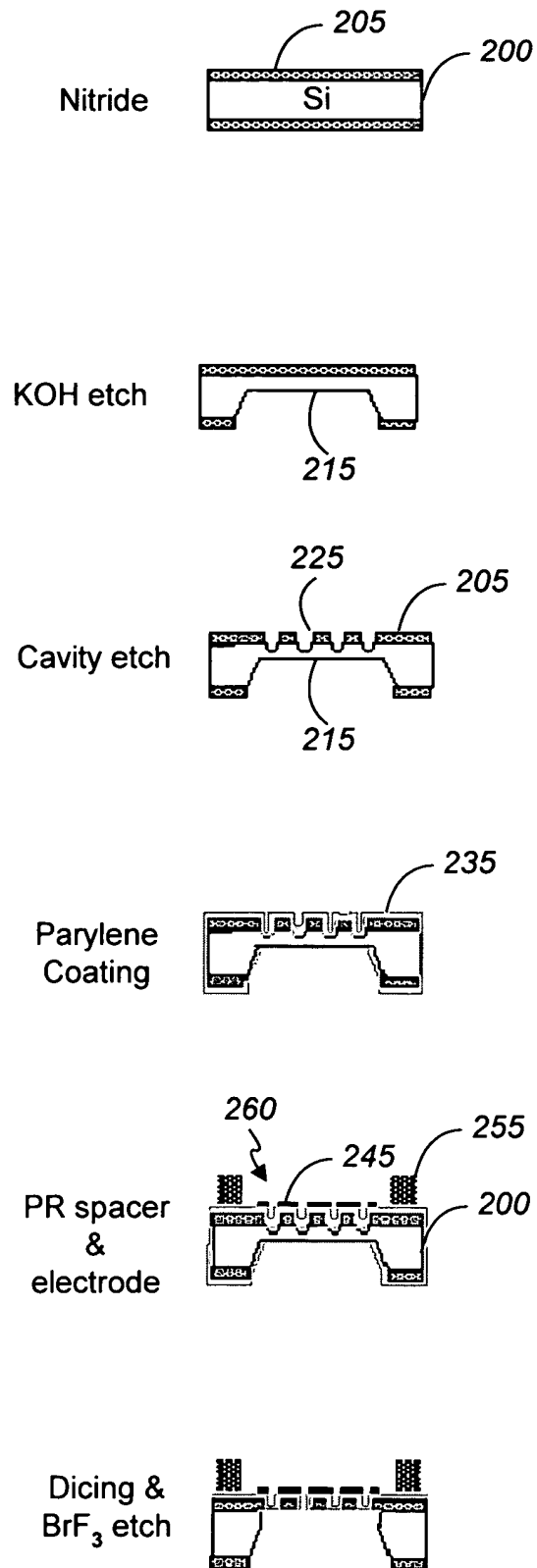
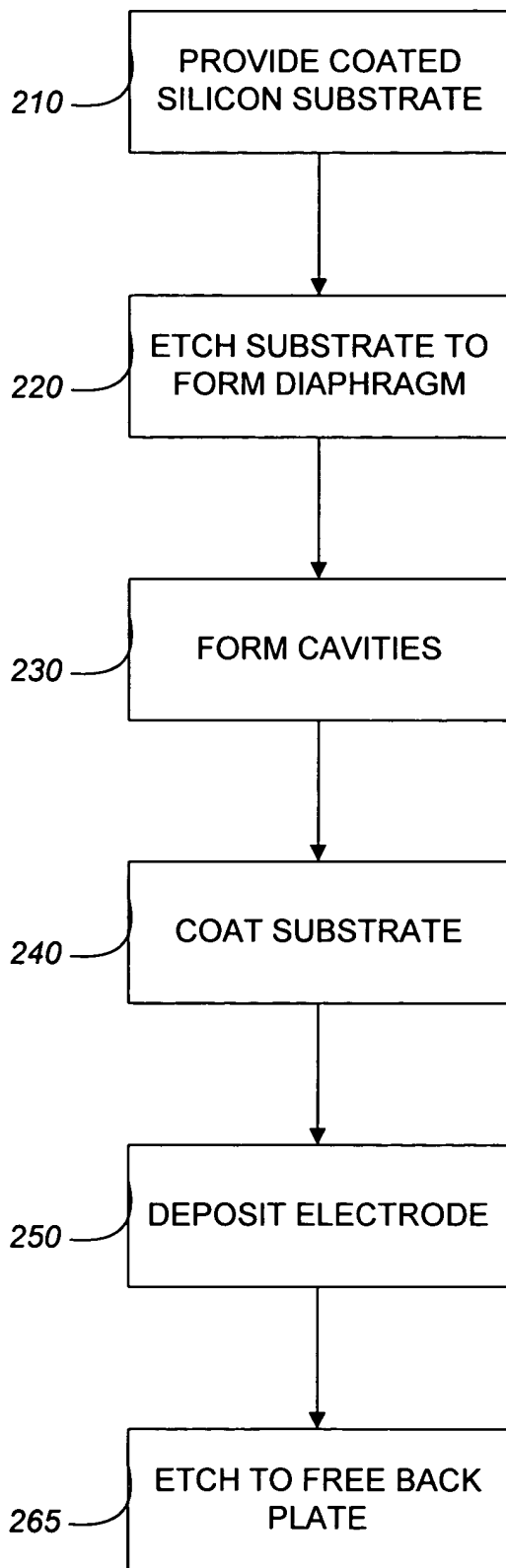


FIG. 2

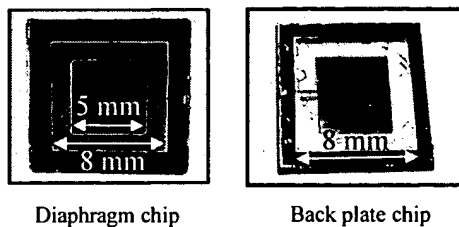


FIG. 3

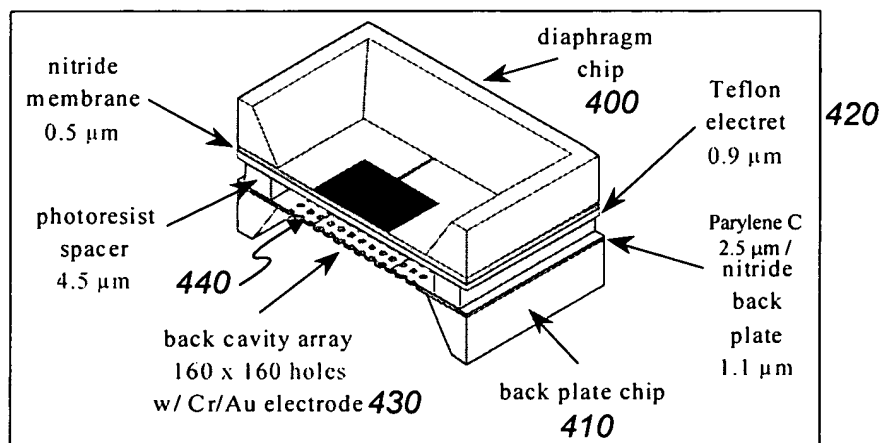


FIG. 4

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graph TD; 610[PROVIDE COATED SILICON SUBSTRATE] --> 620[BACK-ETCH TO FORM MEMBRANE]; 620 --> 635[COAT SUBSTRATE]; 635 --> 640[DEPOSIT ELECTRODE]; 640 --> 645[ETCH SILICON DIAPHRAGM]; 645 --> 655[SPIN ON DIELECTRIC FILM]; 655 --> 665[FORM ELECTRET];
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610 PROVIDE COATED SILICON SUBSTRATE

620 BACK-ETCH TO FORM MEMBRANE

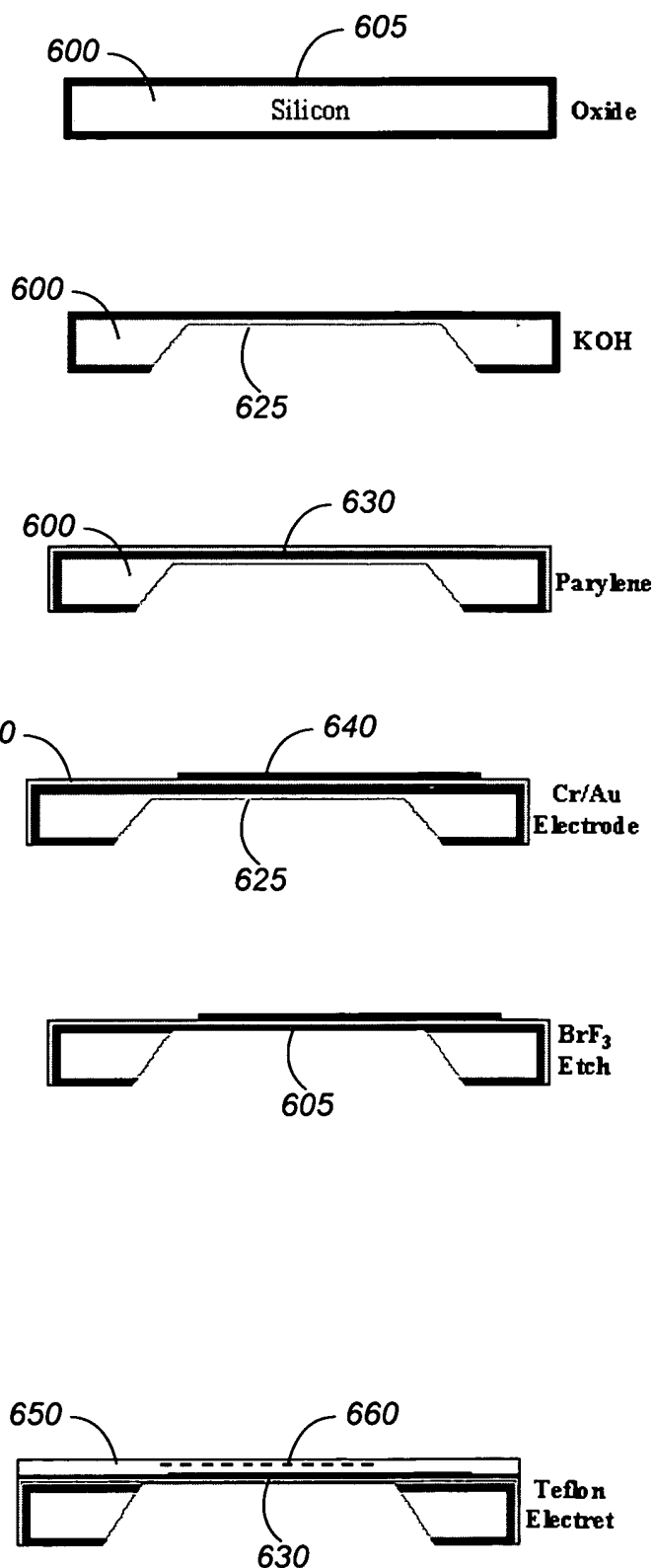
635 COAT SUBSTRATE

640 DEPOSIT ELECTRODE

645 ETCH SILICON DIAPHRAGM

655 SPIN ON DIELECTRIC FILM

665 FORM ELECTRET



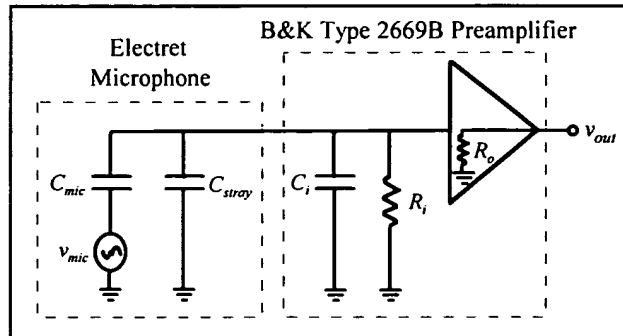


FIG. 5

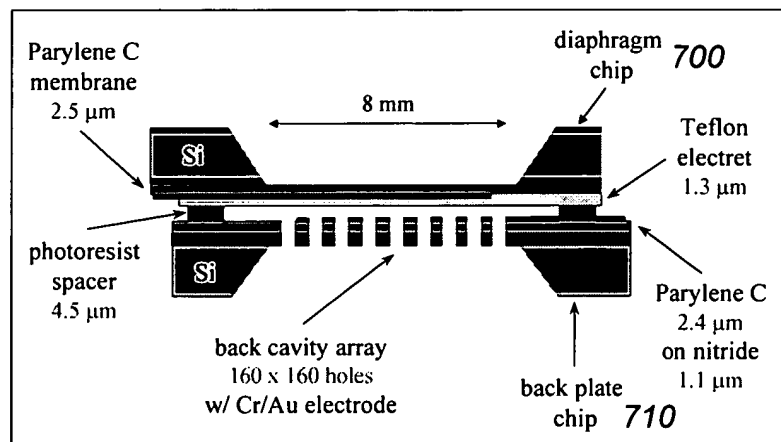


FIG. 7